

# Ion Implantation

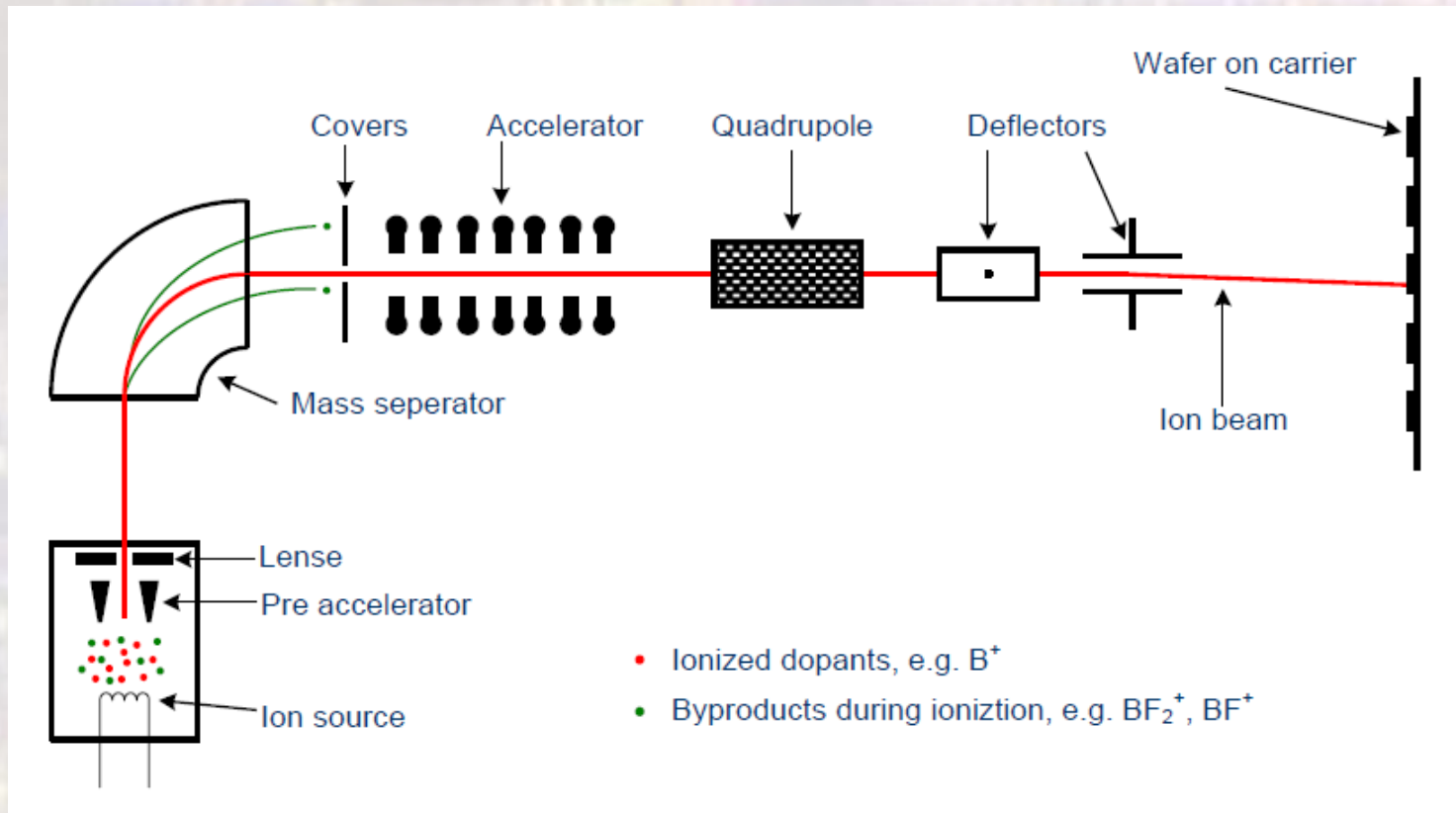
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# Ion Implantation

- Ion Implantation
  - Charged dopants (ions) are accelerated in an electric field and irradiated onto the wafer
  - Penetration is well controlled by modulating the electric field
  - Minimal lateral movement
  - Low temperature process
    - Does not disturb prior work
  - Causes lattice damage
    - Can be annealed with later temperature processing

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Src: [www.halbleiter.org](http://www.halbleiter.org)

# Ion Implantation

- Ion Implantation vs. Diffusion

